MAX9982ETP Rev. A

RELIABILITY REPORT

FOR

MAX9982ETP

PLASTIC ENCAPSULATED DEVICES

February 10, 2004

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

Written by

01

Jim Pedicord Quality Assurance Reliability Lab Manager

Reviewed by

Bryan J. Preeshl Quality Assurance Executive Director

Conclusion

The MAX9982 successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

Table of Contents

I.Device Description II.Manufacturing Information III.Packaging Information IV.Die Information V.Quality Assurance Information VI.Reliability Evaluation

.....Attachments

I. Device Description

A. General

The MAX9982 fully integrated SiGe mixer is optimized to meet the demanding requirements of GSM850, GSM900, and CDMA850 base-station receivers. Each high-linearity device includes a local oscillator (LO) switch, LO driver, and active mixer. On-chip baluns are also integrated to allow for single-ended RF and LO inputs. Since the active mixer provides 2dB of conversion gain, the device effectively replaces the IF amplifier stage, which typically follows most passive mixer implementations.

The MAX9982 provides exceptional linearity with an input IP3 of greater than +26dBm. The integrated LO driver allows for a wide range of LO drive levels from -5dBm to +5dBm. In addition, the built-in switch enables rapid LO selection of less than 250ns, as needed for GSM frequency-hopping applications.

The MAX9982 is available in a 20-pin QFN package (5mm x 5mm) with an exposed paddle and is specified over the - 40°C to +85°C extended temperature range.

B. Absolute Maximum Ratings

ltem	Rating
VCC	-0.3V to +5.5V
IF+, IF-, RFBIAS, LOSEL	-0.3V to (VCC + 0.3V)
ТАР	+5.0V
RFBIAS Current	5mA
RF, LO1, LO2 Input Power	+20dBm
Operating Temperature Range	-40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C
Lead Temperature (soldering, 10s)	+300°C
20-Pin QFN	1.66W
Derates above +70°C	
20-Pin QFN	20.8mW/°C

II. Manufacturing Information

A. Description/Function:	825MHz to 915MHz, SiGe High-Linearity Active Mixer
B. Process:	GST4-MB20 Bi-CMOS Process
C. Number of Device Transistors:	179
D. Fabrication Location:	Oregon, USA
E. Assembly Location:	Thailand
F. Date of Initial Production:	July, 2002

III. Packaging Information

A. Package Type:	20-Pin QF	N (5x5)
B. Lead Frame:	Copper	
C. Lead Finish:	Solder Pla	ite
D. Die Attach:	Silver-Fille	d Epoxy
E. Bondwire:	Gold (1.0 r	nil dia.)
F. Mold Material:	Epoxy with	n silica filler
G. Assembly Diagram	# 05-9000-	-0846
H. Flammability Rating	: Class UL9	4-V0
I. Classification of Mois per JEDEC standard	sture Sensitivity JESD22-A112: Level 1	
IV. Die Information		
A. Dimensions:	97 x 61 m	ls
B. Passivation:	Si ₃ N ₄ (Silic	on nitride)
C. Interconnect:	Au	
D. Backside Metallizat	ion: None	
E. Minimum Metal Wic	th: 1.2 micron	s (as drawn) Metal 1, 2 & 3 5.6 microns (as drawn) Metal 4
F. Minimum Metal Spa	cing: 1.6 micron	s (as drawn) Metal 1, 2 & 3, 4.2 microns (as drawn) Metal 4
G. Bondpad Dimension	ns: 5 mil.	
H. Isolation Dielectric:	SiO ₂	
I. Die Separation Meth	od: Wafer Sav	l l

V. Quality Assurance Information

Α.	Quality Assurance Contacts:	Jim Pedicord	(Manager, Reliability Operations)
		Bryan Preeshl	(Executive Director of QA)
		Kenneth Huening	(Vice President)

- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 150°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate (λ) is calculated as follows:

 $\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 9823 \times 90 \times 2}$ (Chi square value for MTTF upper limit) Temperature Acceleration factor assuming an activation energy of 0.8eV $\lambda = 10.78 \times 10^{-9}$ $\lambda = 10.78 \text{ F.I.T.}$ (60% confidence level @ 25°C)

This low failure rate represents data collected from Maxim's reliability qualification and monitor programs. Maxim also performs weekly Burn-In on samples from production to assure reliability of its processes. The reliability required for lots which receive a burn-in qualification is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on rejects from lots exceeding this level. The attached Burn-In Schematic #06-7063 shows the static circuit used for this test. Maxim also performs 1000 hour life test monitors quarterly for each process. This data is published in the Product Reliability Report (**RR-B2A**).

B. Moisture Resistance Tests

Maxim evaluates pressure pot stress from every assembly process during qualification of each new design. Pressure Pot testing must pass a 20% LTPD for acceptance. Additionally, industry standard 85°C/85%RH or HAST tests are performed quarterly per device/package family.

C. E.S.D. and Latch-Up Testing

The CR02 die type has been found to have all pins able to withstand a transient pulse of +/-1000V, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit).

Latch-Up testing has shown that this device withstands a current of ±250mA.

Table 1Reliability Evaluation Test Results

MAX9982ETP

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test	t (Note 1)			
	Ta = 150°C Biased Time = 192 hrs.	DC Parameters & functionality	45	0
Moisture Testir	ng (Note 2)			
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
Mechanical Str	ess (Note 2)			
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification packages. Note 2: Generic package/process data.

Attachment #1

TABLE II.	Pin combination to be tested.	1/ 2/

	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)		
1.	All pins except V _{PS1} <u>3/</u>	All V _{PS1} pins		
2.	All input and output pins	All other input-output pins		

- 1/ Table II is restated in narrative form in 3.4 below.
- $\overline{2}$ / No connects are not to be tested.
- $\overline{\underline{3}}$ Repeat pin combination I for each named Power supply and for ground

(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_{S}$, $-V_{S}$, V_{REF} , etc).

- 3.4 <u>Pin combinations to be tested.</u>
 - a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
 - b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1}, or V_{SS2} or V_{SS3} or V_{CC1}, or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
 - c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.



5x5x0.8 MM QFN THIN PKG.

EXPOSED PAD PKG.

			DIE I.D.	
			N/C 16	
1 1 2 1 N/C 3 1 4 1				15 14 N/C 13 N/C 12 N/C
N/C 5 				
CAV./PAD_SIZE:	PKG.	310NATUKES		CONFIDENTIAL & PROPRIETARY BOND DIAGRAM #: REV:
138×138	DESIGN			105-9000-0846 A



DOCUMENT I.D. 06-7063